

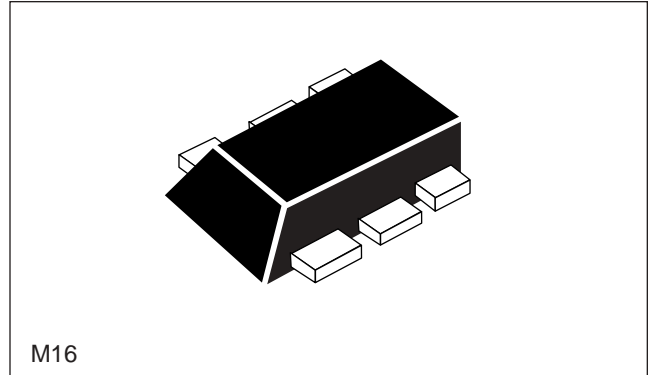


**NEC's NPN SiGe
HIGH FREQUENCY TRANSISTOR**

NESG2101M16

FEATURES

- **HIGH BREAKDOWN VOLTAGE SiGe TECHNOLOGY**
V_{CEO} = 5 V (Absolute Maximum)
- **HIGH OUTPUT POWER:**
P_{1dB} = 21 dBm at 2 GHz
- **LOW NOISE FIGURE:**
NF = 0.9 dB at 2 GHz
NF = 0.6 dB at 1 GHz
- **HIGH MAXIMUM STABLE POWER GAIN:**
MSG = 17 dB at 2 GHz
- **LOW PROFILE M16 PACKAGE:**
6-pin lead-less minimold



DESCRIPTION

NEC's NESG2101M16 is fabricated using NEC's high voltage Silicon Germanium process (UHS2-HV), and is designed for a wide range of applications including low noise amplifiers, medium power amplifiers, and oscillators

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

PART NUMBER PACKAGE OUTLINE		NESG2101M16 M16				
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX	
RF	P _{1dB}	Output Power at 1 dB Compression Point V _{CE} = 3.6 V, I _{CQ} = 10 mA, f = 2 GHz, Z _S = Z _{SOPT} , Z _L = Z _{LOPT}	dBm	21		
	G _L	Linear Gain, V _{CE} = 3.6 V, I _{CQ} = 10 mA, f = 2 GHz,	dB	15		
	NF	Noise Figure at V _{CE} = 2 V, I _C = 10 mA, f = 2 GHz, Z _S = Z _{SOPT} , Z _L = Z _{LOPT}	dB		0.9	1.2
	G _a	Associated Gain at V _{CE} = 2 V, I _C = 10 mA, f = 2 GHz, Z _S = Z _{SOPT} , Z _L = Z _{LOPT}	dB	11.0	13.0	
	NF	Noise Figure at V _{CE} = 2 V, I _C = 7mA, f = 1 GHz, Z _S = Z _{SOPT} , Z _L = Z _{LOPT}	dB		0.6	
	G _a	Associated Gain at V _{CE} = 2 V, I _C = 7 mA, f = 1 GHz, Z _S = Z _{SOPT} , Z _L = Z _{LOPT}	dB		19.0	
	MSG	Maximum Stable Gain ¹ at V _{CE} = 3 V, I _C = 50 mA, f = 2 GHz	dB	14.5	17.0	
	S _{21E} ²	Insertion Power Gain at V _{CE} = 3 V, I _C = 50 mA, f = 2 GHz	dB	11.5	13.5	
	f _T	Gain Bandwidth Product at V _{CE} = 3 V, I _C = 50 mA, f = 2 GHz	GHz	14	17	
	C _{re}	Reverse Transfer Capacitance ² at V _{CB} = 2 V, I _E = 0 mA, f = 1 MHz	pF		0.4	0.5
DC	I _{CBO}	Collector Cutoff Current at V _{CB} = 5V, I _E = 0	nA			100
	I _{EBO}	Emitter Cutoff Current at V _{EB} = 1 V, I _C = 0	nA			100
	h _{FE}	DC Current Gain ³ at V _{CE} = 2 V, I _C = 15 mA		130	190	260

Notes:

1. $MSG = \left| \frac{S_{21}}{S_{12}} \right|$
2. Collector to base capacitance when the emitter pin is grounded.
3. Pulsed measurement, pulse width ≤ 350 μs, duty cycle ≤ 2 %.

ABSOLUTE MAXIMUM RATINGS¹ (T_A = 25°C)

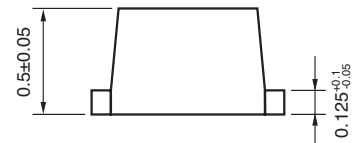
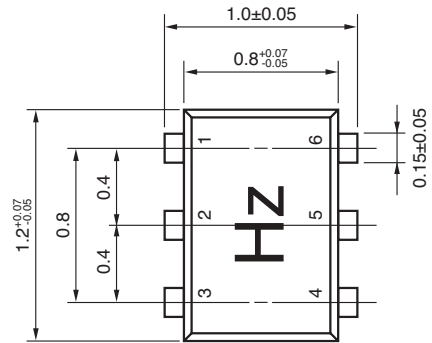
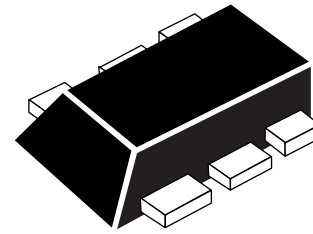
SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{CB0}	Collector to Base Voltage	V	13.0
V _{CE0}	Collector to Emitter Voltage	V	5.0
V _{EBO}	Emitter to Base Voltage	V	1.5
I _c	Collector Current	mA	100
P _T ²	Total Power Dissipation	mW	190
T _J	Junction Temperature	°C	150
T _{STG}	Storage Temperature	°C	-65 to +150

Note:

1. Operation in excess of any one of these parameters may result in permanent damage.
2. Mounted on 1.08 cm² x 1.0 mm (t) glass epoxy PCB.

OUTLINE DIMENSIONS (Units in mm)

**PACKAGE OUTLINE M16
6-PIN LEAD-LESS MINIMOLD**



ORDERING INFORMATION

PART NUMBER	QUANTITY	SUPPLYING FORM
NESG2101M16-T3	10 K pcs reel	Pin 1 (Collector), Pin 6 (Emitter) face the perforation side of the tape

PIN CONNECTIONS

- | | |
|--------------|------------|
| 1. Collector | 4. Base |
| 2. Emitter | 5. Emitter |
| 3. Emitter | 6. Emitter |

Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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